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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



1N4531; 1N4532 High-speed diodes

Product data sheet Supersedes data of April 1996 1996 Sep 03



High-speed diodes

1N4531; 1N4532

FEATURES

Hermetically sealed leaded glass SOD68 (DO-34) package

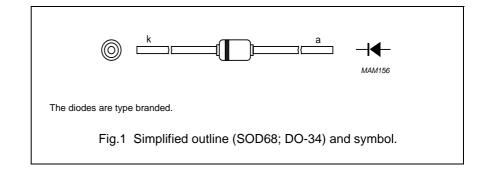
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

- · High-speed switching
- Protection diodes in reed relays.

DESCRIPTION

The 1N4531, 1N4532 are high-speed switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD68 (DO-34) packages.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		-	75	V
V_R	continuous reverse voltage		-	75	V
I _F	continuous forward current	see Fig.2	-	200	mA
I _{FRM}	repetitive peak forward current		-	450	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	Α
		t = 1 ms	_	1	Α
		t = 1 s	_	0.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	_	500	mW
T _{stg}	storage temperature		-65	+200	°C
T _j	junction temperature		_	200	°C

High-speed diodes

1N4531; 1N4532

ELECTRICAL CHARACTERISTICS

 $T_j = 25$ °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _F	forward voltage	I _F = 10 mA; see Fig.3	_	1000	mV
I _R	reverse current	see Fig.5			
	IN4531	V _R = 20 V	_	25	nA
		V _R = 20 V; T _j = 150 °C	_	50	μΑ
	IN4532	V _R = 50 V	_	100	nA
		V _R = 50 V; T _j = 150 °C	_	100	μΑ
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6			
	IN4531		_	4	pF
	IN4532		_	2	pF
t _{rr}	reverse recovery time	when switched from I _F = 10 mA to			
	IN4531	$I_R = 60 \text{ mA}$; $R_L = 100 \Omega$; measured	_	4	ns
	IN4532 at $I_R = 1$ mA; see Fig.7	_	2	ns	
	reverse recovery time	when switched from $I_F = 10$ mA to			
	IN4532	I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	_	4	ns
V _{fr}	forward recovery voltage	when switched from I_F = 100 mA; $t_r \le 30$ ns; see Fig.8	-	3	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	lead length 5 mm	120	K/W
R _{th j-a}	thermal resistance from junction to ambient	lead length 5 mm; note 1	350	K/W

Note

1. Device mounted on a printed circuit-board without metallization pad.

High-speed diodes

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GRAPHICAL DATA

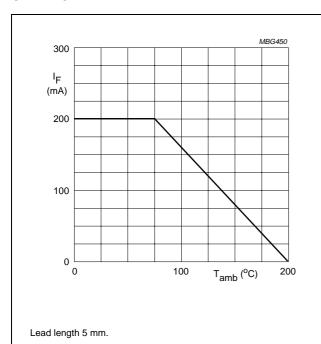
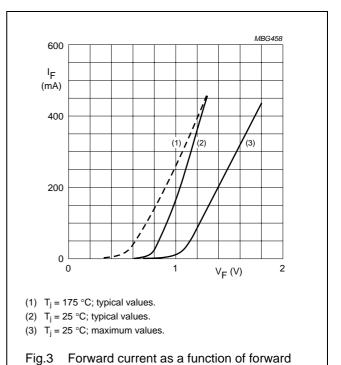
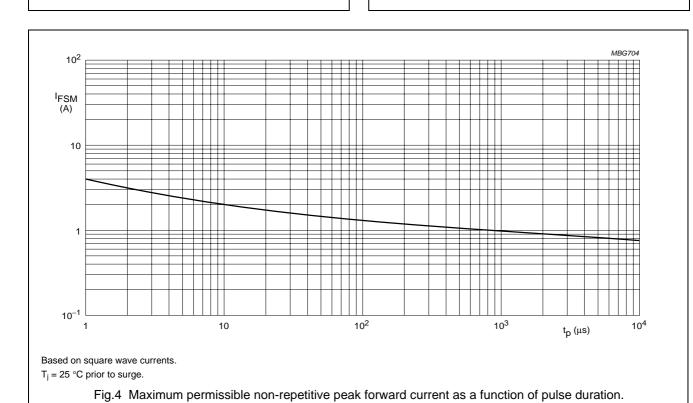


Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.

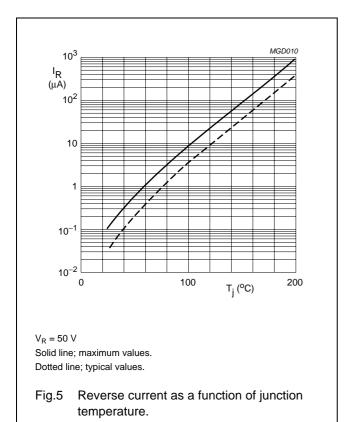


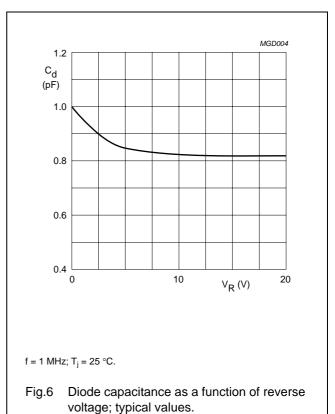
voltage.



High-speed diodes

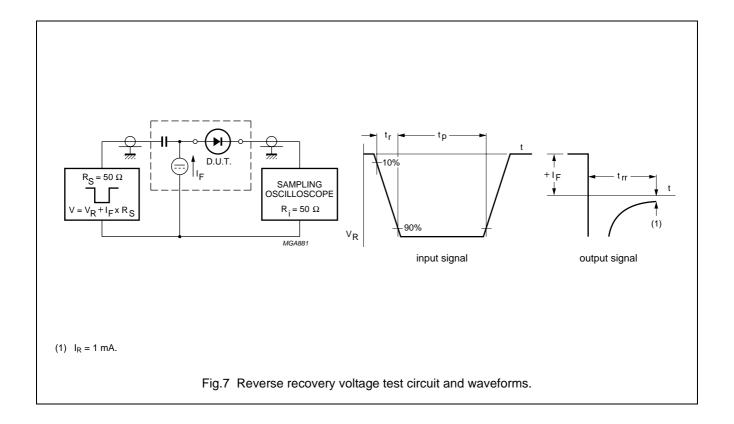
1N4531; 1N4532

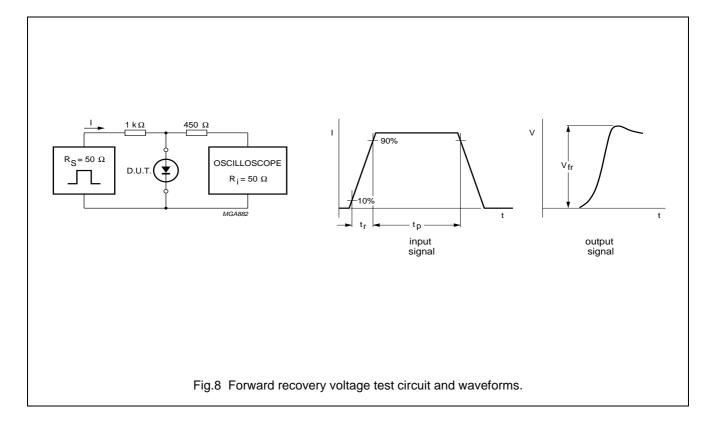




High-speed diodes

1N4531; 1N4532

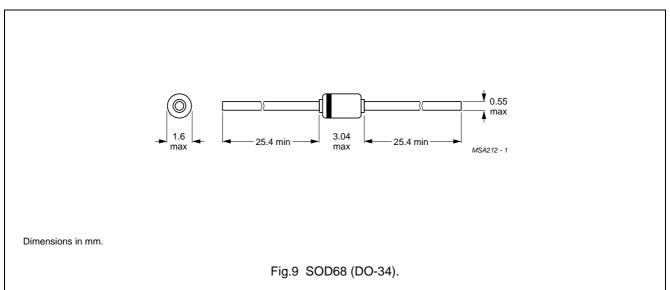




High-speed diodes

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PACKAGE OUTLINE



High-speed diodes

1N4531; 1N4532

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: http://www.nxp.com

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